CLAIM CHANGES

1. (Previously Cancelled)

2. (Previously Cancelled)

3. (Previously Cancelled)

4. (Previously Cancelled)

5. (Previously Cancelled)

6. (Previously Cancelled)

7. (Previously Cancelled)

8. (Previously Cancelled)

9. (Cancelled)

10. (Cancelled)

11. (Currently Amended) A method of manufacturing a semiconductor device, comprising:

~~the step of~~ forming a gate insulating film on a semiconductor substrate;

~~the step of~~ forming a gate electrode on the gate insulating film;

~~the step of~~ forming a source-drain diffusion layer in the semiconductor substrate;

~~the step of forming~~ depositing a film which inhibits silicidation on the source-drain diffusion layer by a CVD method;

~~the step of~~ forming a film of a metal having a high melting point on the gate electrode and on the source-drain diffusion layer; and

~~the step of~~ converting the film of the high melting point metal into a silicide film to form a silicide film selectively on the gate electrode and on the source-drain diffusion layer.

12. (Original) The method of manufacturing a semiconductor device according to claim 11, wherein said film serving to inhibit said silicidation is selected from the group consisting of an oxide film and a nitride film.

13. (Withdrawn from consideration) A method of manufacturing a semiconductor device, comprising:

the step of forming a gate insulating film on a semiconductor substrate;

the step of forming a gate electrode on the gate insulating film;

the step of forming a source-drain diffusion layer in the semiconductor substrate;

the step of forming an insulating film on the gate electrode and on the source-drain diffusion layer;

the step of thinning the insulating film so as to expose the surface of the gate electrode with the source-drain diffusion layer kept covered with the insulating-film;

the step of introducing atoms into a region around the surface of the gate electrode so as to make the upper portion of the gate electrode amorphous;

the step of removing the insulating film positioned on the source-drain diffusion layer;

the step of forming a film of a metal having a high melting point on the gate-electrode and on the source-drain diffusion layer; and

the step of converting the film of the high melting point metal into a silicide film to form a silicide film selectively on the gate electrode and on the source-drain diffusion layer.

14. (Withdrawn from consideration) The method of manufacturing a semiconductor device according to claim 13, wherein said atoms introduced into a surface region of said gate electrode are selected from the group consisting of boron, germanium, silicon, arsenic and antimony.

15. (Withdrawn from consideration) A method of manufacturing a semiconductor device, comprising:

the step of forming a gate insulating film on a semiconductor substrate;

the step of forming an amorphous silicon film having a shape of a gate electrode on the gate insulating film;

the step of forming a source-drain diffusion layer in the semiconductor substrate; the step of forming a film of a metal having a high melting point on the amorphous silicon film and on the source-drain diffusion layer; and

the step of converting the film of the high melting point metal into a silicide film to form a silicide film selectively on the amorphous silicon film and on the source-drain diffusion layer.

16. (Withdrawn from consideration) The method of manufacturing a semiconductor device according to claim 15, wherein said step of forming said silicide film comprises a heat treatment for converting said film of a high melting point metal into a silicide film, and said amorphous silicon film is converted into a polycrystalline silicon film by said heat treatment.

17. (Withdrawn from consideration) A method of manufacturing a semiconductor device, comprising:

the step of forming a gate insulating film on a semiconductor substrate;

the step of forming a gate electrode on the gate insulating film;

the step of forming a source-drain diffusion layer in the semiconductor substrate;

the step of forming a silicide film selectively on the gate electrode and on the source-drain diffusion layer;

the step of forming an insulating film on the silicide film positioned on the gate electrode and on the source-drain diffusion layer;

the step of thinning the insulating film to expose the surface of the silicide film positioned on the gate electrode with the silicide film, which is positioned on the source-drain diffusion layer, kept covered with the insulating film; and

the step of further forming a silicide film on the surface of the exposed silicide film.

18. (Withdrawn from consideration) A method of manufacturing a semiconductor device, comprising:

the step of forming a gate insulating film on a semiconductor substrate;

the step of forming a gate electrode on the gate insulating film;

the step of forming a source-drain diffusion layer in the semiconductor substrate;

the step of forming a film of a metal having a high melting point on the gate electrode and on the source-drain diffusion layer;

the step of converting the film of the high melting point metal into a silicide film so as to form a silicide film selectively on the gate electrode and on the source-drain diffusion layer;

the step of forming an insulating film on the silicide film positioned on the gate electrode and on the source-drain diffusion layer;

the step of thinning the insulating film to expose the surface of the silicide film positioned on the gate electrode with the silicide film, which is positioned on the source-drain diffusion layer, kept covered with the insulating film; the step of forming a film of a high melting point metal on the silicide film positioned on the gate electrode; and

the step of converting the film of the high melting point metal into a silicide film so as to form a silicide film selectively on the silicide film formed previously on the gate electrode.

19. (Withdrawn from consideration) The semiconductor device according to any one of claims 9, 11, 13, 15, 17, and 18, wherein said silicide film formed on said gate electrode is at least 1.2 times as thick as the silicide film formed on the source-drain diffusion layer.